

To our customers,

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## Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: <http://www.renesas.com>

April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (<http://www.renesas.com>)

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### MOS FIELD EFFECT TRANSISTOR NP80N055MDG, NP80N055NDG, NP80N055PDG

#### SWITCHING N-CHANNEL POWER MOS FET

#### DESCRIPTION

The NP80N055MDG, NP80N055NDG, and NP80N055PDG are N-channel MOS Field Effect Transistors designed for high current switching applications.

#### ORDERING INFORMATION

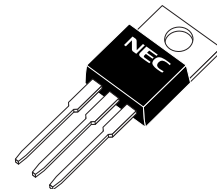
| PART NUMBER                            | LEAD PLATING  | PACKING     | PACKAGE                     |
|----------------------------------------|---------------|-------------|-----------------------------|
| NP80N055MDG-S18-AY <small>Note</small> | Pure Sn (Tin) | Tube        | TO-220 (MP-25K) typ. 1.9 g  |
| NP80N055NDG-S18-AY <small>Note</small> |               | 50 p/tube   | TO-262 (MP-25SK) typ. 1.8 g |
| NP80N055PDG-E1B-AY <small>Note</small> |               | Tape        | TO-263 (MP-25ZP) typ. 1.5 g |
| NP80N055PDG-E2B-AY <small>Note</small> |               | 1000 p/reel |                             |

**Note** Pb-free (This product does not contain Pb in the external electrode.)

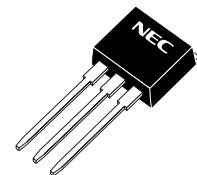
#### FEATURES

- Logic level
- Super low on-state resistance
  - NP80N055MDG, NP80N055NDG
    - $R_{DS(on)1} = 6.9 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 40 \text{ A)}$
    - $R_{DS(on)2} = 11.2 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 35 \text{ A)}$
  - NP80N055PDG
    - $R_{DS(on)1} = 6.6 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 40 \text{ A)}$
    - $R_{DS(on)2} = 10.9 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 35 \text{ A)}$
- High current rating
  - $I_{D(DC)} = \pm 80 \text{ A}$
- Low input capacitance
  - $C_{iss} = 4600 \text{ pF TYP.}$
- Designed for automotive application and AEC-Q101 qualified

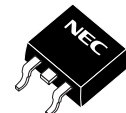
(TO-220)



(TO-262)



(TO-263)



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**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C)**

|                                                 |                       |             |    |
|-------------------------------------------------|-----------------------|-------------|----|
| Drain to Source Voltage (V <sub>GS</sub> = 0 V) | V <sub>DSS</sub>      | 55          | V  |
| Gate to Source Voltage (V <sub>bs</sub> = 0 V)  | V <sub>GSS</sub>      | ±20         | V  |
| Drain Current (DC) (T <sub>C</sub> = 25°C)      | I <sub>D(DC)</sub>    | ±80         | A  |
| Drain Current (pulse) <sup>Note1</sup>          | I <sub>D(pulse)</sub> | ±200        | A  |
| Total Power Dissipation (T <sub>C</sub> = 25°C) | P <sub>T1</sub>       | 115         | W  |
| Total Power Dissipation (T <sub>A</sub> = 25°C) | P <sub>T2</sub>       | 1.8         | W  |
| Channel Temperature                             | T <sub>ch</sub>       | 175         | °C |
| Storage Temperature                             | T <sub>stg</sub>      | -55 to +175 | °C |
| Repetitive Avalanche Current <sup>Note2</sup>   | I <sub>AR</sub>       | 33          | A  |
| Repetitive Avalanche Energy <sup>Note2</sup>    | E <sub>AR</sub>       | 111         | mJ |

**Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%

**2.** T<sub>ch</sub> ≤ 150°C, R<sub>G</sub> = 25 Ω

**THERMAL RESISTANCE**

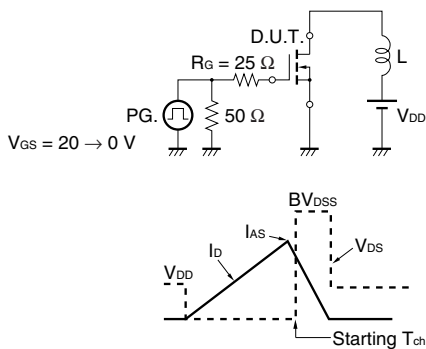
|                                       |                       |      |      |
|---------------------------------------|-----------------------|------|------|
| Channel to Case Thermal Resistance    | R <sub>th(ch-C)</sub> | 1.30 | °C/W |
| Channel to Ambient Thermal Resistance | R <sub>th(ch-A)</sub> | 83.3 | °C/W |

ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

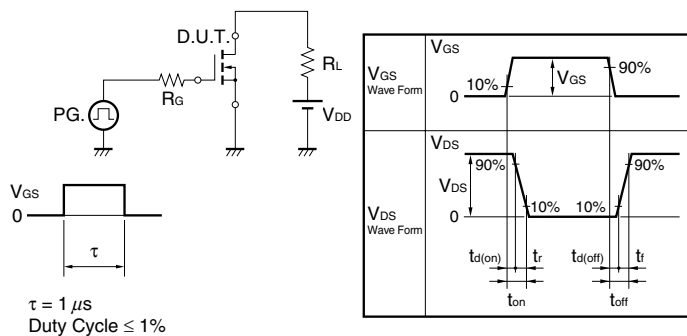
| CHARACTERISTICS                                     | SYMBOL               | TEST CONDITIONS                                                            | MIN. | TYP. | MAX. | UNIT |
|-----------------------------------------------------|----------------------|----------------------------------------------------------------------------|------|------|------|------|
| Zero Gate Voltage Drain Current                     | I <sub>DSS</sub>     | V <sub>DS</sub> = 55 V, V <sub>GS</sub> = 0 V                              |      |      | 1    | μA   |
| Gate Leakage Current                                | I <sub>GSS</sub>     | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V                             |      |      | ±100 | nA   |
| Gate to Source Threshold Voltage                    | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                | 1.4  |      | 2.5  | V    |
| Forward Transfer Admittance <sup>Note</sup>         | y <sub>fs</sub>      | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 35 A                               | 25   | 64   |      | S    |
| Drain to Source On-state Resistance <sup>Note</sup> | R <sub>DS(on)1</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A<br>NP80N055MDG, NP80N055NDG  |      | 5.4  | 6.9  | mΩ   |
|                                                     |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A<br>NP80N055PDG               |      | 4.8  | 6.6  | mΩ   |
|                                                     | R <sub>DS(on)2</sub> | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 35 A<br>NP80N055MDG, NP80N055NDG |      | 6.3  | 11.2 | mΩ   |
|                                                     |                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 35 A<br>NP80N055PDG              |      | 5.9  | 10.9 | mΩ   |
| Input Capacitance                                   | C <sub>iss</sub>     | V <sub>DS</sub> = 25 V,                                                    |      | 4600 | 6900 | pF   |
| Output Capacitance                                  | C <sub>oss</sub>     | V <sub>GS</sub> = 0 V,                                                     |      | 390  | 590  | pF   |
| Reverse Transfer Capacitance                        | C <sub>rss</sub>     | f = 1 MHz                                                                  |      | 240  | 430  | pF   |
| Turn-on Delay Time                                  | t <sub>d(on)</sub>   | V <sub>DD</sub> = 28 V, I <sub>D</sub> = 40 A,                             |      | 17   | 37   | ns   |
| Rise Time                                           | t <sub>r</sub>       | V <sub>GS</sub> = 10 V,                                                    |      | 13   | 33   | ns   |
| Turn-off Delay Time                                 | t <sub>d(off)</sub>  | R <sub>G</sub> = 0 Ω                                                       |      | 77   | 154  | ns   |
| Fall Time                                           | t <sub>f</sub>       |                                                                            |      | 7    | 18   | ns   |
| Total Gate Charge                                   | Q <sub>G</sub>       | V <sub>DD</sub> = 44 V,                                                    |      | 90   | 135  | nC   |
| Gate to Source Charge                               | Q <sub>GS</sub>      | V <sub>GS</sub> = 10 V,                                                    |      | 13   |      | nC   |
| Gate to Drain Charge                                | Q <sub>GD</sub>      | I <sub>D</sub> = 80 A                                                      |      | 26   |      | nC   |
| Body Diode Forward Voltage <sup>Note</sup>          | V <sub>F(S-D)</sub>  | I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V                               |      | 0.95 | 1.5  | V    |
| Reverse Recovery Time                               | t <sub>rr</sub>      | I <sub>F</sub> = 80 A, V <sub>GS</sub> = 0 V,                              |      | 38   |      | ns   |
| Reverse Recovery Charge                             | Q <sub>rr</sub>      | di/dt = 100 A/μs                                                           |      | 45   |      | nC   |

**Note** Pulsed test

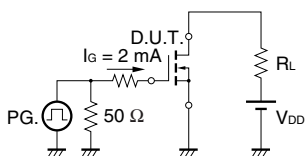
TEST CIRCUIT 1 AVALANCHE CAPABILITY



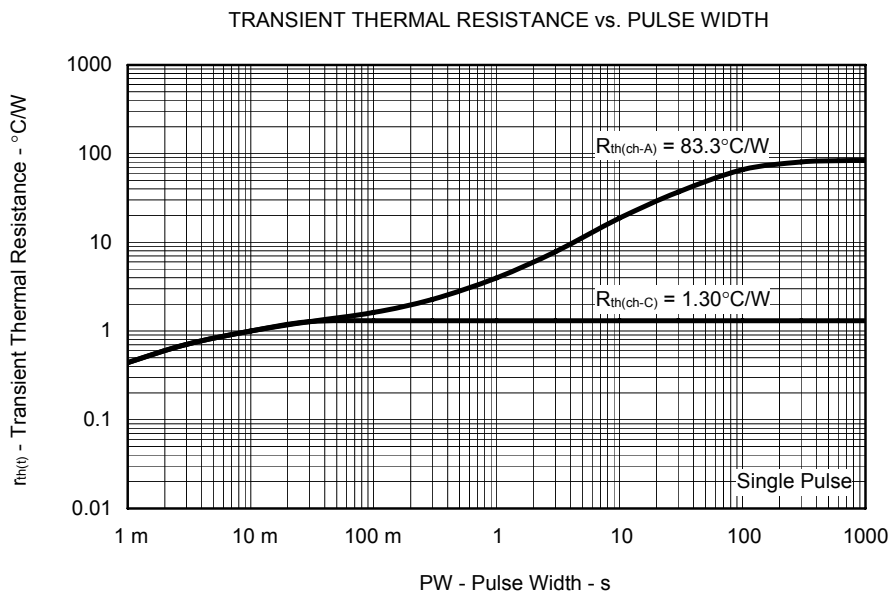
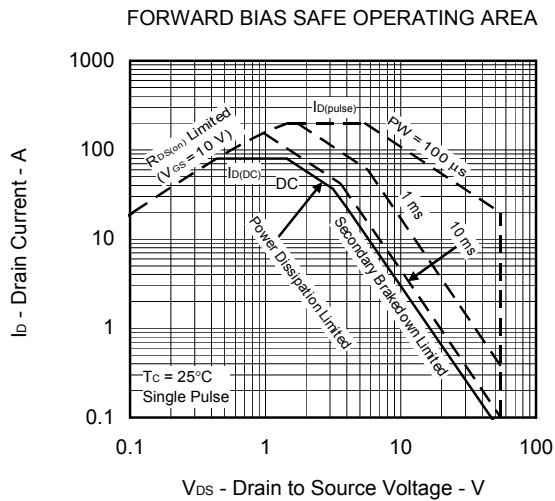
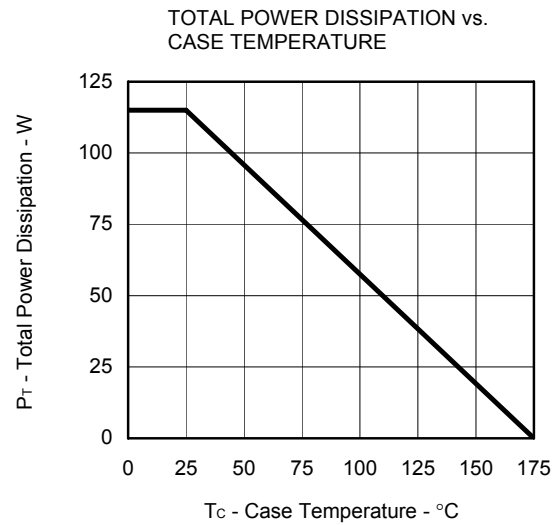
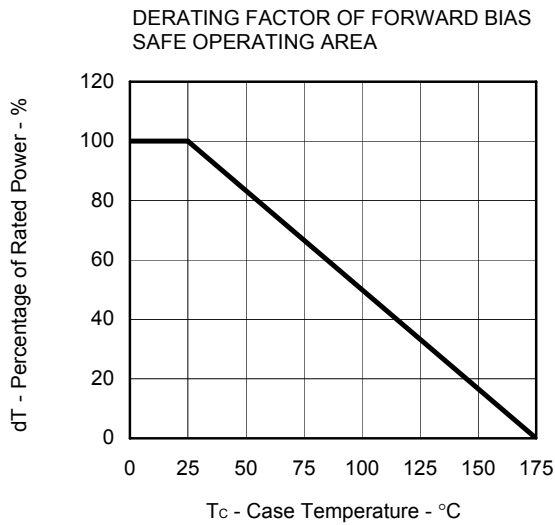
TEST CIRCUIT 2 SWITCHING TIME

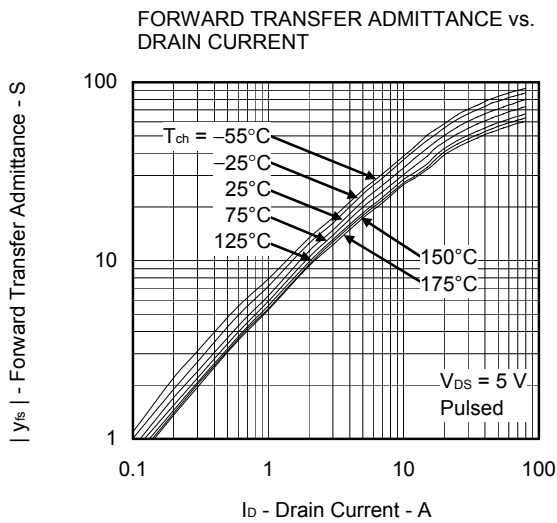
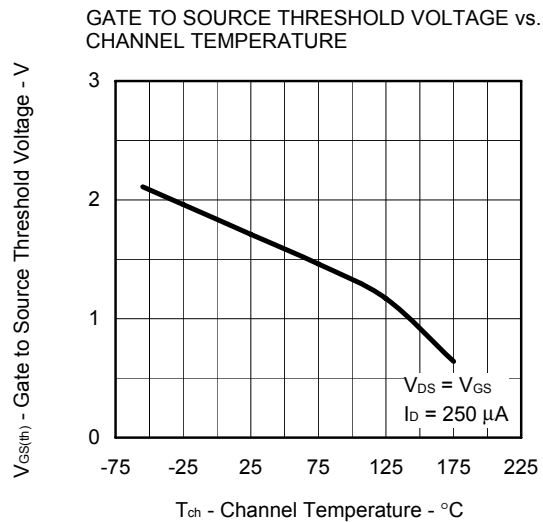
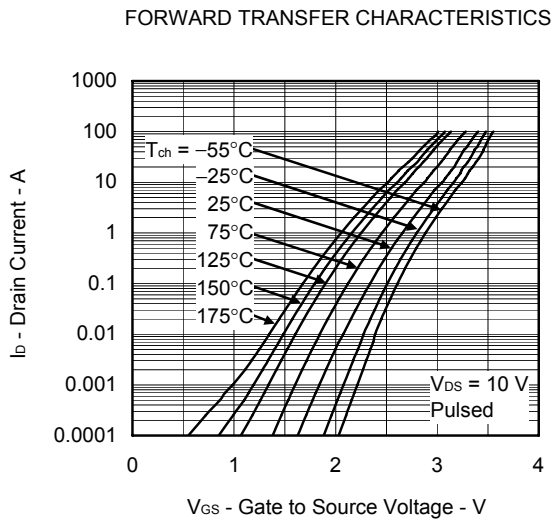
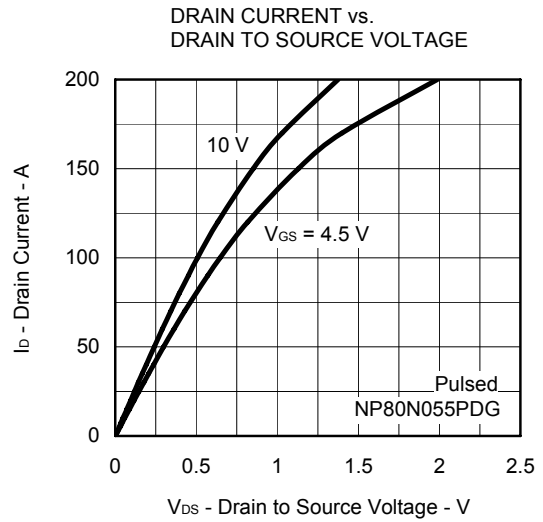
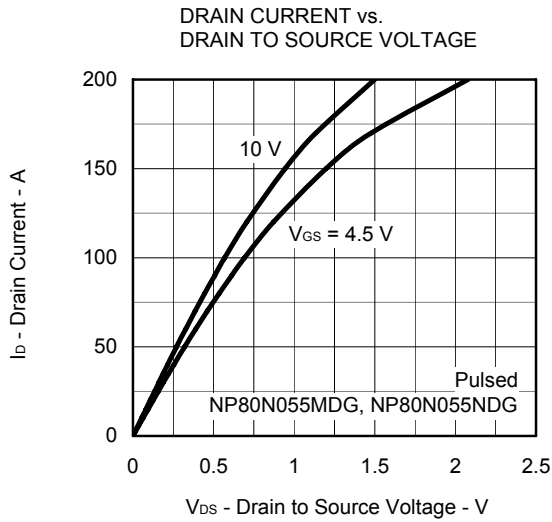


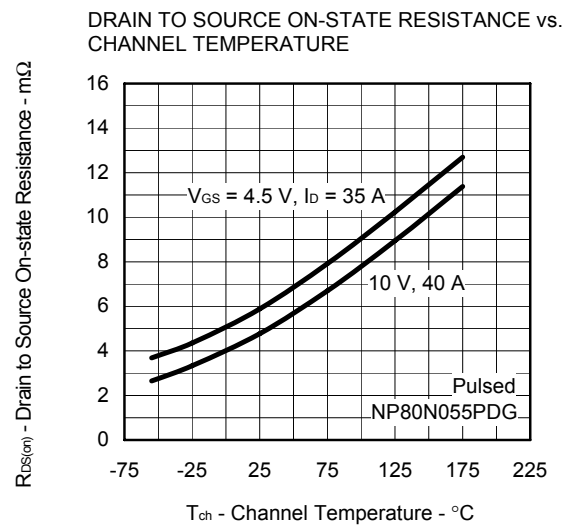
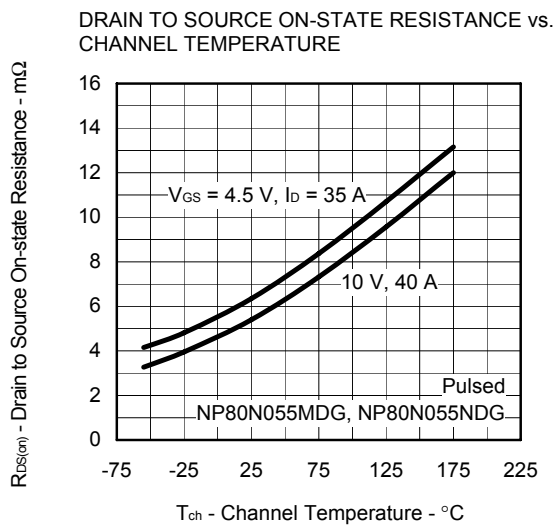
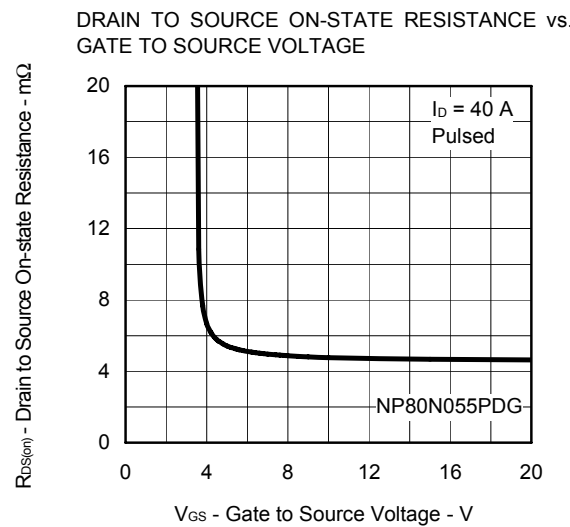
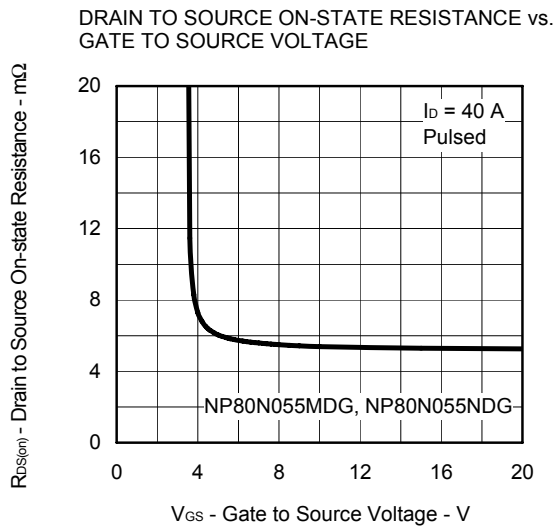
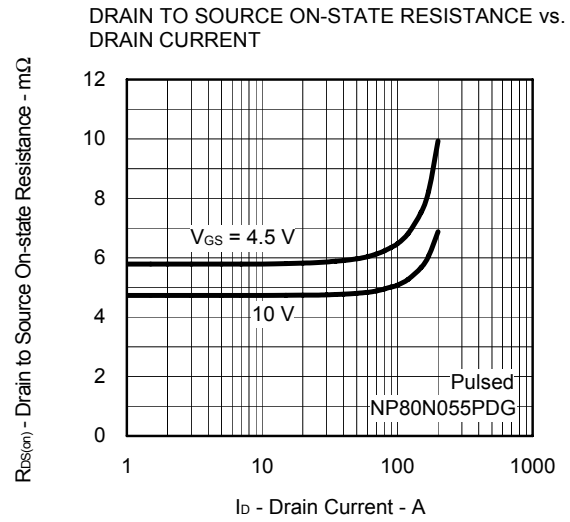
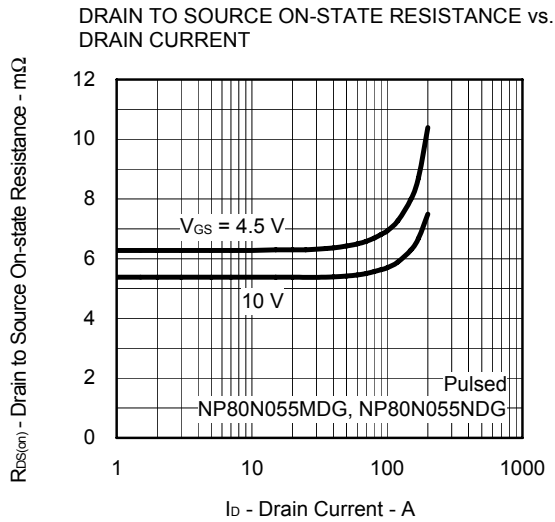
TEST CIRCUIT 3 GATE CHARGE



TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

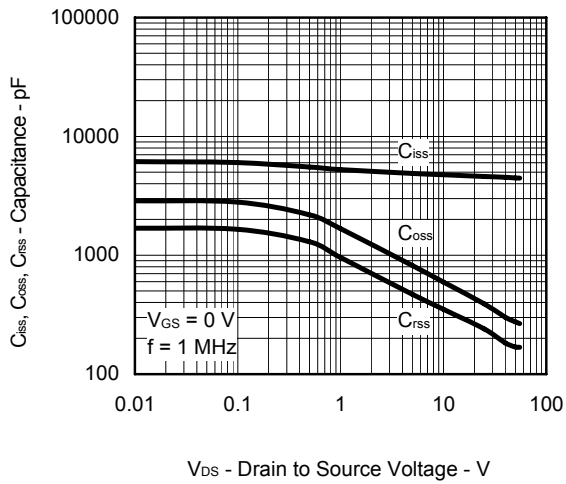




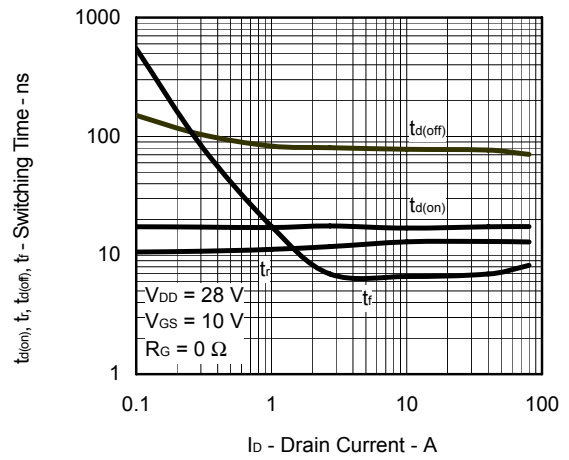




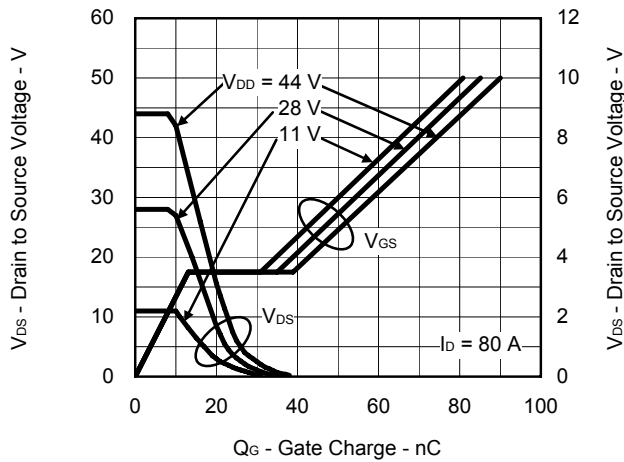
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



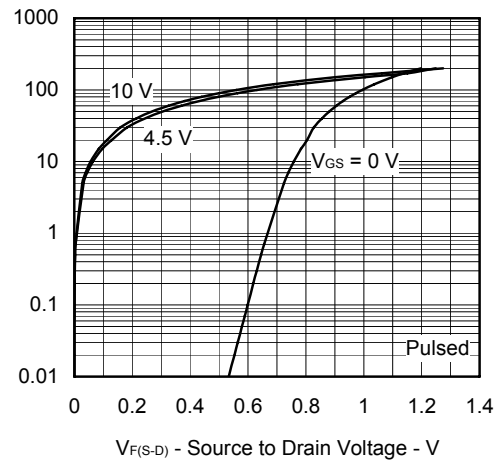
SWITCHING CHARACTERISTICS



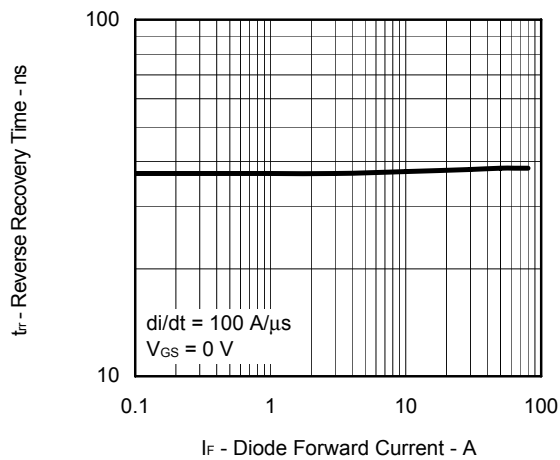
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

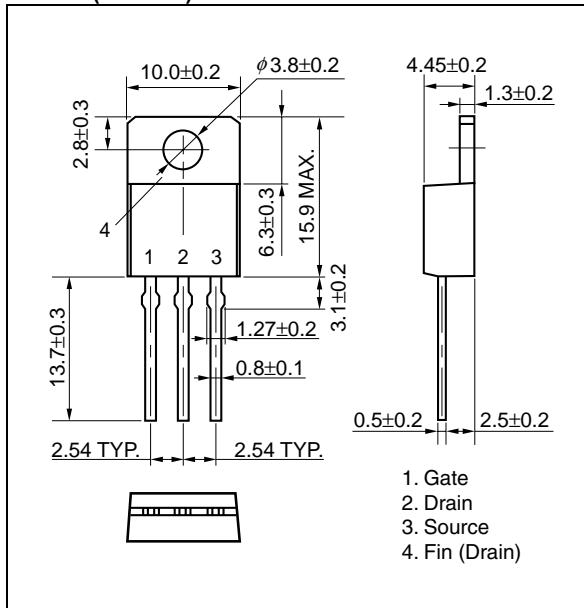


REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

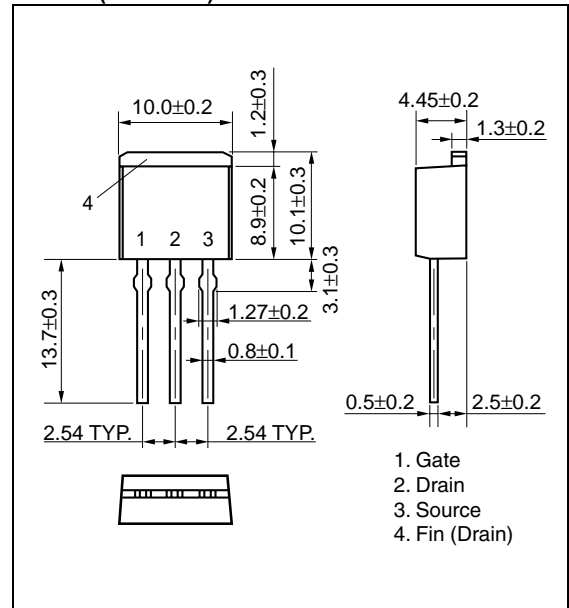


PACKAGE DRAWINGS (Unit: mm)

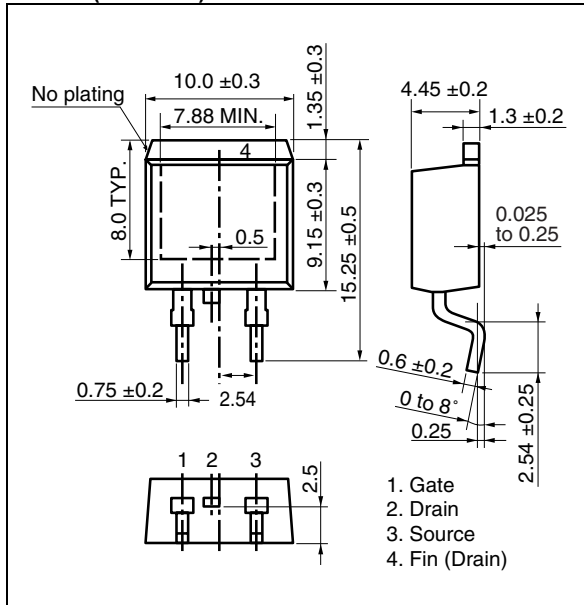
TO-220 (MP-25K)



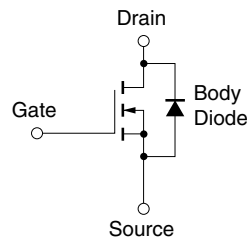
TO-262 (MP-25SK)



TO-263 (MP-25ZP)



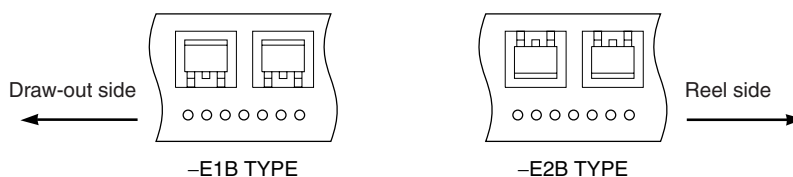
EQUIVALENT CIRCUIT



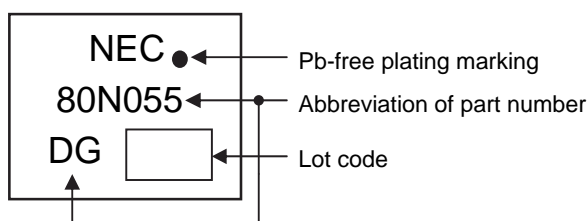
**Remark** Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

**TAPE INFORMATION (NP80N055PDG)**

There are two types (-E1B, -E2B) of taping depending on the direction of the device.



**MARKING INFORMATION**



**RECOMMENDED SOLDERING CONDITIONS**

These products should be soldered and mounted under the following recommended conditions.

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For technical information, see the following website.

Semiconductor Device Mount Manual (<http://www.necel.com/pkg/en/mount/index.html>)

| Soldering Method                                               | Soldering Conditions                                                                                                                                                                                                                                                                                                                                               | Recommended Condition Symbol |
|----------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|
| Infrared reflow<br>NP80N055PDG                                 | Maximum temperature (Package's surface temperature): 260°C or below<br>Time at maximum temperature: 10 seconds or less<br>Time of temperature higher than 220°C: 60 seconds or less<br>Preheating time at 160 to 180°C: 60 to 120 seconds<br>Maximum number of reflow processes: 3 times<br>Maximum chlorine content of rosin flux (percentage mass): 0.2% or less | IR60-00-3                    |
| Wave soldering<br>NP80N055MDG,<br>NP80N055NDG                  | Maximum temperature (Solder temperature): 260°C or below<br>Time: 10 seconds or less<br>Maximum chlorine content of rosin flux: 0.2% (wt.) or less                                                                                                                                                                                                                 | THDWS                        |
| Partial heating<br>NP80N055MDG,<br>NP80N055NDG,<br>NP80N055PDG | Maximum temperature (Pin temperature): 350°C or below<br>Time (per side of the device): 3 seconds or less<br>Maximum chlorine content of rosin flux: 0.2% (wt.) or less                                                                                                                                                                                            | P350                         |

**Caution Do not use different soldering methods together (except for partial heating).**

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"Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support).

"Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC Electronics products is "Standard" unless otherwise expressly specified in NEC Electronics data sheets or data books, etc. If customers wish to use NEC Electronics products in applications not intended by NEC Electronics, they must contact an NEC Electronics sales representative in advance to determine NEC Electronics' willingness to support a given application.

(Note)

(1) "NEC Electronics" as used in this statement means NEC Electronics Corporation and also includes its majority-owned subsidiaries.

(2) "NEC Electronics products" means any product developed or manufactured by or for NEC Electronics (as defined above).